Abstracts

Bandpass Microwave Electron-Bombarded Semiconductor Amplifiers

P.S. Carter, Jr., J.A. Long and L.A. Roberts. "Bandpass Microwave Electron-Bombarded Semiconductor Amplifiers." 1974 S-MTT International Microwave Symposium Digest of Technical Papers 74.1 (1974 [MWSYM]): 348-350.

This paper introduces a new type of microwave amplifier which employs as its active element electron-bombarded semiconductor diodes. This amplifier is capable of achieving both high peak and high average powers. Useful characteristics include its broad bandwidth (several GHz are possible), high efficiency (in the 50 to 60 percent range), and very low harmonic distortion. These characteristics make this amplifier extremely attractive for use in a variety of communications, radar, and laboratory test applications.

❑ Return to main document.